NSN 5961-01-505-1436

Photo Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

Between 0.232 inches and 0.270 inches

Terminal Length:

0.500 inches

Overall Diameter:

Between 0.179 inches and 0.187 inches

End Application:

Maintenance recorder unit, tornado

Internal Configuration:

Junction contact

Mounting Method:

Terminal

Terminal Circle Diameter:

0.100 inches

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

50.0 collector to base voltage, dc and 30.0 collector to emitter voltage, dc and 5.0 emitter to base voltage, dc and 5.0 emitter to collector voltage, dc

Current Rating Per Characteristic:

50.00 milliamperes source cutoff current

Power Rating Per Characteristic:

250.0 milliwatts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius junction

Product Name:

Npn silicon phototransistors

Special Features:

Narrow receiving angle; variety of sensitivity ranges

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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